

**REVISION HISTORY**

REVISION	DESCRIPTION	DATE
Rev. 0.9	Original.	Apr. 26,2001
Rev. 1.0	Revised - The test condition of $I_{CC1}$ and $I_{CC2}$ - Symbols CE#,OE# and WE# $\Rightarrow$ $\overline{CE}$ , $\overline{OE}$ and $\overline{WE}$ - The ordering information of package ,STSOP-1 is revised as STSOP.	May. 14,2001
Rev. 1.1	Revised - Improve $I_{DR}$ from 20 $\mu$ A to 10 $\mu$ A (LL-version , max.) - Package outline dimension	May 14,2002
Rev. 1.2	Revised - Add Standby Current $I_{SB1}=20\mu$ A for special requirement ( LL-version , max. ) - Ordering information in Standby Current column ( maximum typical ) - Standby Current in FEATURES section Rev.1.1 : 3mA (typical) normal Rev.1.2 : 0.3mA (typical) normal - Cycle time condition of $I_{CC2}$ in DC electrical characteristics Rev.1.1 : Tcycle=1ms Rev. 1.2 : Tcycle=1 $\mu$ s - Waveforms - Add under/overshoot range of $V_{IL}$ & $V_{IH}$	May 20,2002
Rev. 1.3	Add order information for lead free product	May 15,2003



FEATURES

- Access time : 35/70ns (max.)
- Low power consumption:  
 Operating : 40/30 mA (typical.)  
 Standby : 0.3mA (typical) normal  
           2uA (typical) L-version  
           1uA (typical) LL-version
- Single 5V power supply
- All inputs and outputs are TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 28-pin 600 mil PDIP  
           28-pin 330 mil SOP  
           28-pin 8mmx13.4mm STSOP

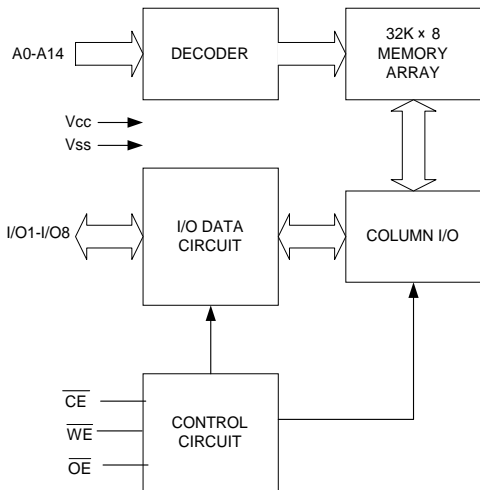
GENERAL DESCRIPTION

The UT62256C is a 262,144-bit low power CMOS static random access memory organized as 32,768 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

The UT62256C is designed for high-speed and low power application. It is particularly well suited for battery back-up nonvolatile memory application.

The UT62256C operates from a single 5V power supply and all inputs and outputs are fully TTL compatible

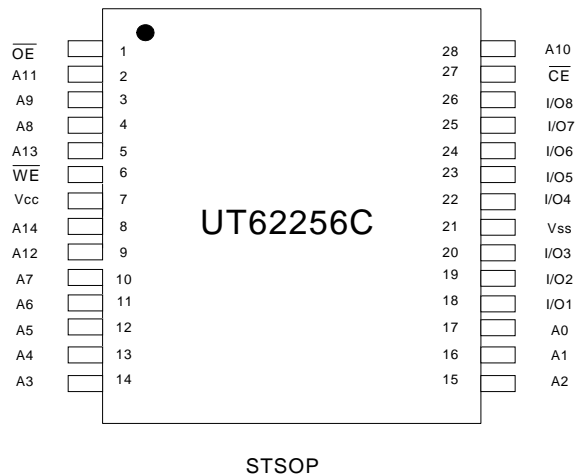
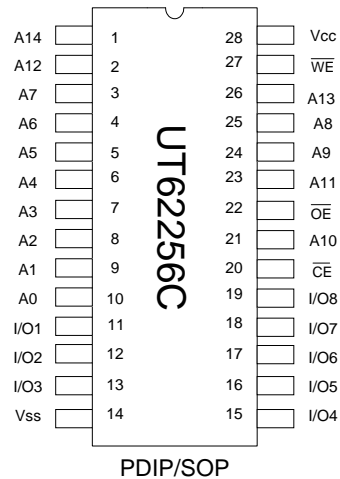
FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A14	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
$V_{CC}$	Power Supply
$V_{SS}$	Ground

PIN CONFIGURATION





**ABSOLUTE MAXIMUM RATINGS\***

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to $V_{SS}$	$V_{TERM}$	-0.5 to +7.0	V
Operating Temperature	$T_A$	0 to +70	
Storage Temperature	$T_{STG}$	-65 to +150	
Power Dissipation	$P_D$	1	W
DC Output Current	$I_{OUT}$	50	mA
Soldering Temperature (under 10 sec)	$T_{solder}$	260	

\*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

**TRUTH TABLE**

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High - Z	$I_{SB}, I_{SB1}$
Output Disable	L	H	H	High - Z	$I_{CC}, I_{CC1}, I_{CC2}$
Read	L	L	H	$D_{OUT}$	$I_{CC}, I_{CC1}, I_{CC2}$
Write	L	X	L	$D_{IN}$	$I_{CC}, I_{CC1}, I_{CC2}$

Note: H =  $V_{IH}$ , L =  $V_{IL}$ , X = Don't care.

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 5V \pm 10\%$ ,  $T_A = 0$  to 70 )

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Input High Voltage	$V_{IH}^{1,2}$		2.2	-	$V_{CC}+0.5$	V	
Input Low Voltage	$V_{IL}^{2}$		-0.5	-	0.8	V	
Input Leakage Current	$I_{LI}$	$V_{SS} \quad V_{IN} \quad V_{CC}$	-1	-	1	$\mu A$	
Output Leakage Current	$I_{LO}$	$V_{SS} \quad V_{IO} \quad V_{CC}$ $\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$	-1	-	1	$\mu A$	
Output High Voltage	$V_{OH}$	$I_{OH} = -1mA$	2.4	-	-	V	
Output Low Voltage	$V_{OL}$	$I_{OL} = 4mA$	-	-	0.4	V	
Operating Power Supply Current	$I_{CC}$	$\overline{CE} = V_{IL}$ , $I_{IO} = 0mA$ , Cycle=Min.	-35	-	40	50	mA
			-70	-	30	40	mA
	$I_{CC1}$	$\overline{CE} = 0.2V$ ; $I_{IO} = 0mA$ other pins at 0.2V or $V_{CC}-0.2V$	Tcycle =500ns	-	-	20	mA
			Tcycle =1 $\mu s$	-	-	10	mA
Standby Power Supply Current	$I_{SB}$	$\overline{CE} = V_{IH}$	normal	-	1	10	mA
					0.3	5	mA
	$I_{SB1}$	$\overline{CE} = V_{IH}$	-L/-LL	-	-	3	mA
			-L	-	2	100	$\mu A$
		-LL	-	1	50	$\mu A$	
					20 <sup>*4</sup>		

Notes:

1. Overshoot :  $V_{CC}+2.0v$  for pulse width less than 10ns.
2. Undershoot :  $V_{SS}-2.0v$  for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.
4.  $I_{SB1}=20\mu A$  for special requirement.

**CAPACITANCE** ( $T_A=25$  ,  $f=1.0\text{MHz}$ )

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	$C_{IN}$	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

**AC TEST CONDITIONS**

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 100\text{pF}$ , $I_{OH}/I_{OL} = -1\text{mA}/4\text{mA}$

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 5V \pm 10\%$  ,  $T_A = 0$  to  $70$  )**(1) READ CYCLE**

PARAMETER	SYMBOL	UT62256C-35		UT62256C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	$t_{RC}$	35	-	70	-	ns
Address Access Time	$t_{AA}$	-	35	-	70	ns
Chip Enable Access Time	$t_{ACE}$	-	35	-	70	ns
Output Enable Access Time	$t_{OE}$	-	25	-	35	ns
Chip Enable to Output in Low Z	$t_{CLZ}^*$	10	-	10	-	ns
Output Enable to Output in Low Z	$t_{OLZ}^*$	5	-	5	-	ns
Chip Disable to Output in High Z	$t_{CHZ}^*$	-	25	-	35	ns
Output Disable to Output in High Z	$t_{OHZ}^*$	-	25	-	35	ns
Output Hold from Address Change	$t_{OH}$	5	-	5	-	ns

**(2) WRITE CYCLE**

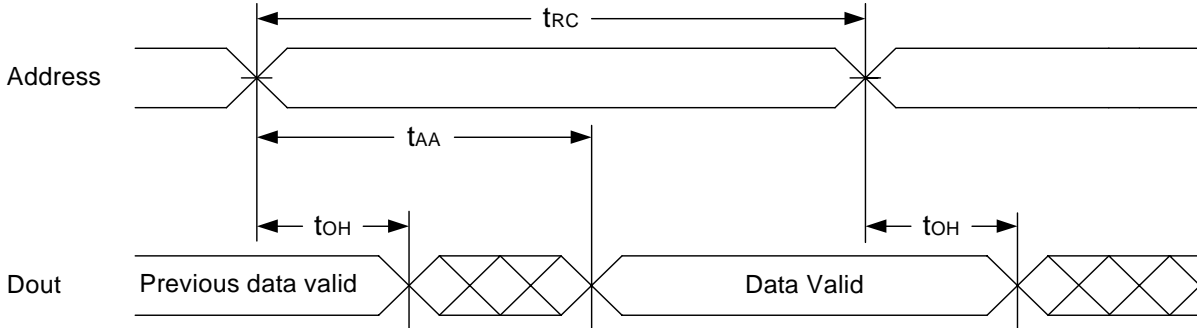
PARAMETER	SYMBOL	UT62256C-35		UT62256C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	$t_{WC}$	35	-	70	-	ns
Address Valid to End of Write	$t_{AW}$	30	-	60	-	ns
Chip Enable to End of Write	$t_{CW}$	30	-	60	-	ns
Address Set-up Time	$t_{AS}$	0	-	0	-	ns
Write Pulse Width	$t_{WP}$	25	-	50	-	ns
Write Recovery Time	$t_{WR}$	0	-	0	-	ns
Data to Write Time Overlap	$t_{DW}$	20	-	30	-	ns
Data Hold from End of Write Time	$t_{DH}$	0	-	0	-	ns
Output Active from End of Write	$t_{OW}^*$	5	-	5	-	ns
Write to Output in High Z	$t_{WHZ}^*$	-	15	-	25	ns

\*These parameters are guaranteed by device characterization, but not production tested.

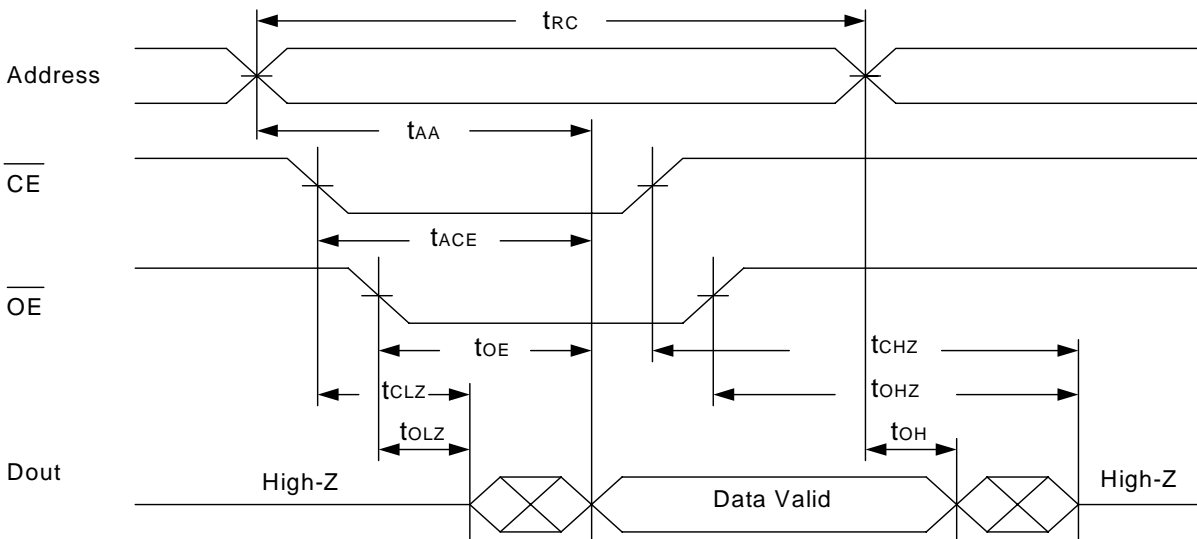


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 ( $\overline{CE}$  and  $\overline{OE}$  Controlled) (1,3,4,5)

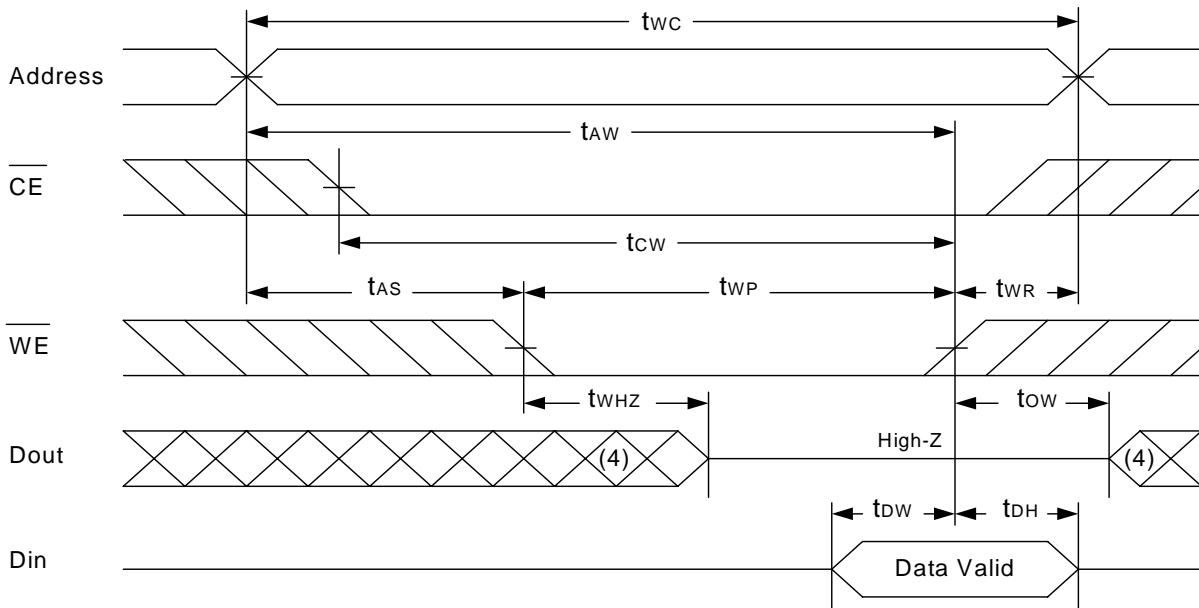


Notes :

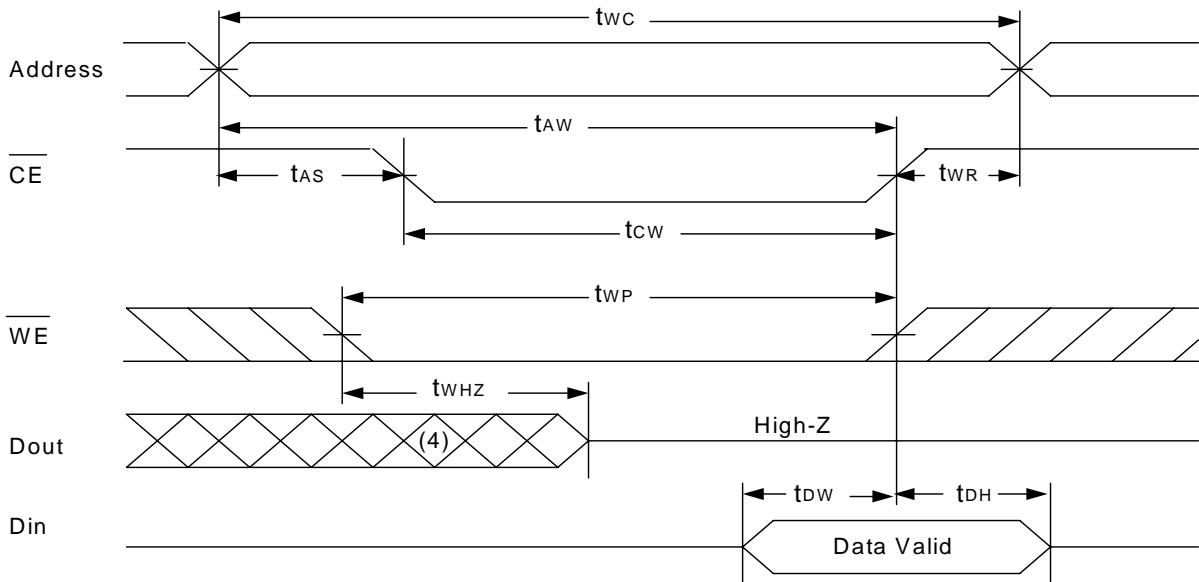
1.  $\overline{WE}$  is high for read cycle.
2. Device is continuously selected  $\overline{OE} = \text{low}$ ,  $\overline{CE} = \text{low}$ .
3. Address must be valid prior to or coincident with  $\overline{CE} = \text{low}$ ; otherwise  $t_{AA}$  is the limiting parameter.
4.  $t_{CLZ}$ ,  $t_{OLZ}$ ,  $t_{CHZ}$  and  $t_{OHZ}$  are specified with  $C_L = 5\text{pF}$ . Transition is measured  $\pm 500\text{mV}$  from steady state.
5. At any given temperature and voltage condition,  $t_{CHZ}$  is less than  $t_{CLZ}$ ,  $t_{OHZ}$  is less than  $t_{OLZ}$ .



WRITE CYCLE 1 ( $\overline{WE}$  Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ( $\overline{CE}$  Controlled) (1,2,5,6)





Notes :

- 1.  $\overline{WE}$ ,  $\overline{CE}$  must be high during all address transitions.
- 2. A write occurs during the overlap of a low  $\overline{CE}$ , low  $\overline{WE}$ .
- 3. During a  $\overline{WE}$  controlled write cycle with  $\overline{OE}$  low,  $t_{WP}$  must be greater than  $t_{WHZ}+t_{DW}$  to allow the drivers to turn off and data to be placed on the bus.
- 4. During this period, I/O pins are in the output state, and input signals must not be applied.
- 5. If the  $\overline{CE}$  low transition occurs simultaneously with or after  $\overline{WE}$  low transition, the outputs remain in a high impedance state.
- 6.  $t_{LOW}$  and  $t_{WHZ}$  are specified with  $C_L = 5pF$ . Transition is measured  $\pm 500mV$  from steady state.

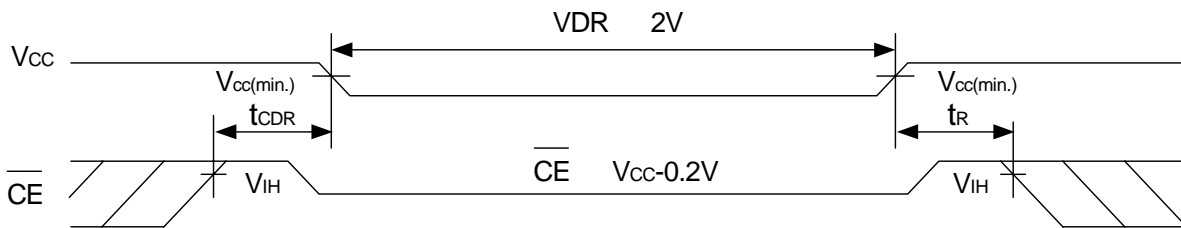
DATA RETENTION CHARACTERISTICS ( $T_A = 0$  to  $70$  )

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	$V_{DR}$	$\overline{CE}$ $V_{CC}-0.2V$	2.0	-	5.5	V
Data Retention Current	$I_{DR}$	$V_{CC}=3V$	- L	1	50	$\mu A$
		$\overline{CE}$ $V_{CC}-0.2V$	- LL	0.5	10	$\mu A$
Chip Disable to Data Retention Time	$t_{CDR}$	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	$t_R$		$t_{RC}^*$	-	-	ns

$t_{RC}^* =$  Read Cycle Time

DATA RETENTION WAVEFORM

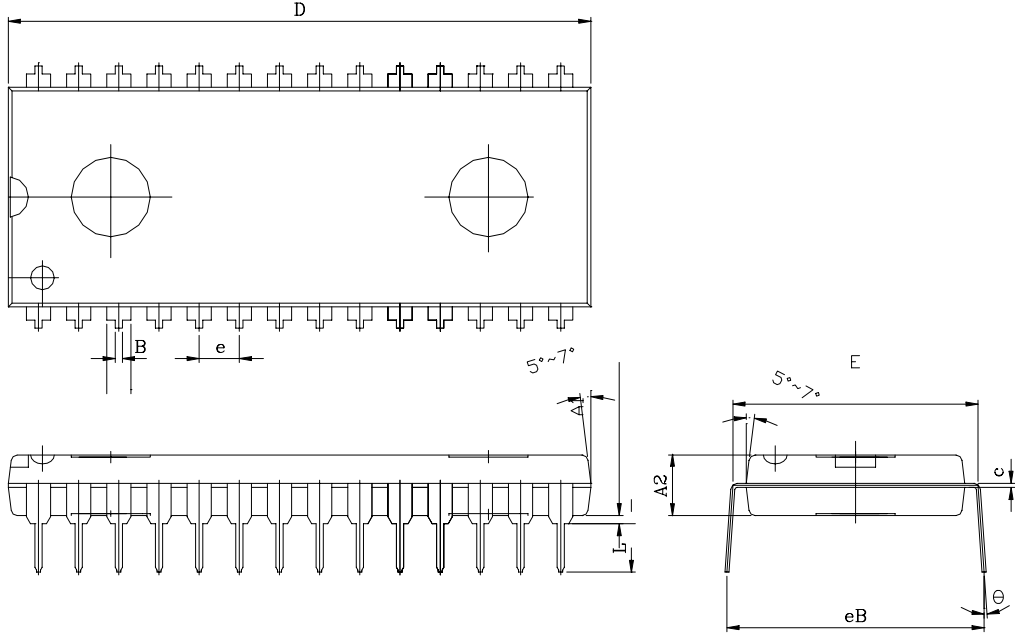
Low Vcc Data Retention Waveform (1) ( $\overline{CE}$  controlled)





**PACKAGE OUTLINE DIMENSION**

**28 pin 600 mil PDIP Package Outline Dimension**

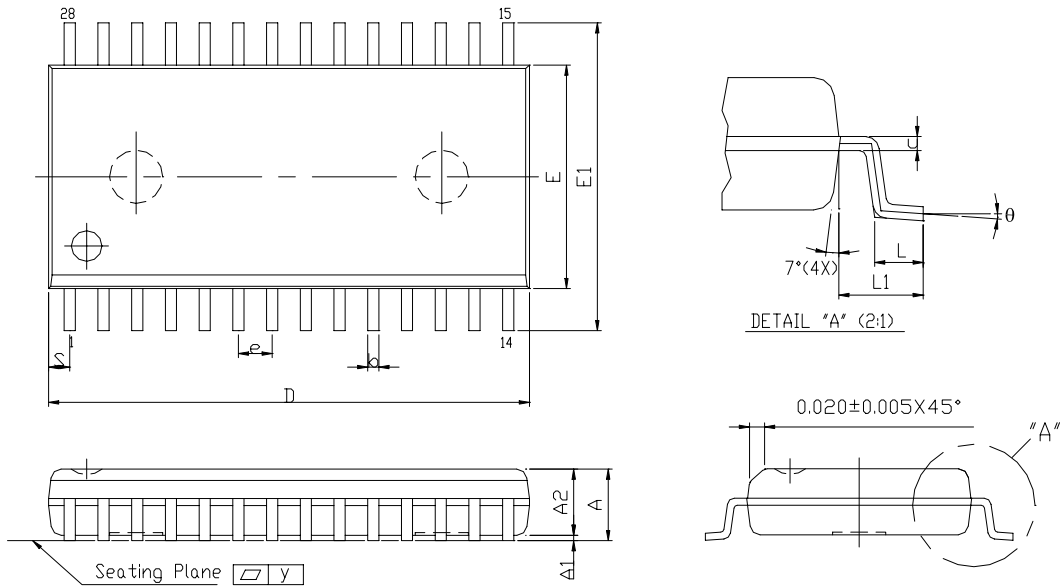


SYMBOL	UNIT	INCH(BASE)	MM(REF)
A1		0.010(MIN)	0.254(MIN)
A2		0.150±0.001	3.810±0.254
B		0.018±0.005	0.457±0.127
c		0.010±0.004	0.254±0.102
D		1.460±0.005	37.084±0.127
E		0.600±0.010	15.240±0.254
e		0.100 (TYP)	2.540(TYP)
eB		0.640±0.03	16.256±0.762
L		0.130±0.010	3.302±0.254
		0°~15°	0°~15°





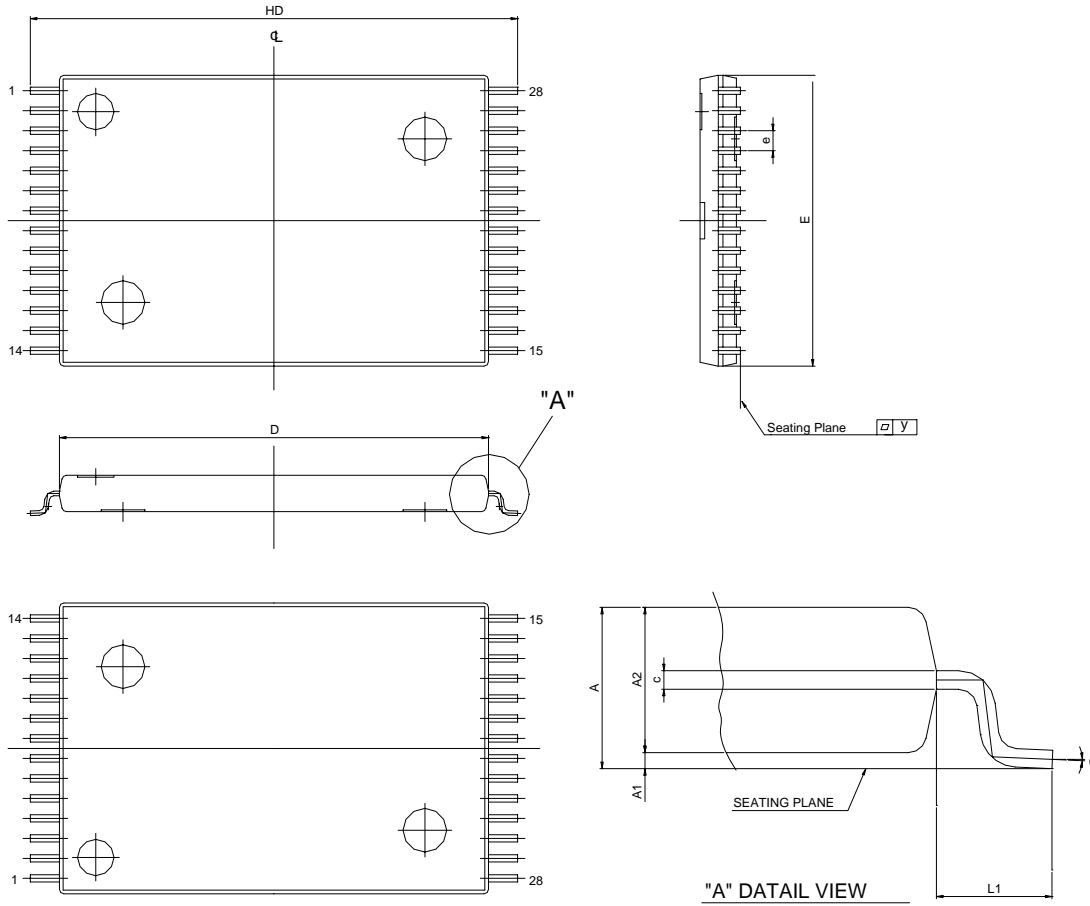
28 pin 330 mil SOP Package Outline Dimension



SYMBOL	UNIT	INCH(BASE)	MM(REF)
A		0.112 (MAX)	2.845 (MAX)
A1		0.004(MIN)	0.102(MIN)
A2		0.098±0.005	2.489±0.127
b		0.016 (TYP)	0.406(TYP)
c		0.010 (TYP)	0.254(TYP)
D		0.713±0.005	18.110±0.127
E		0.331±0.005	8.407±0.127
E1		0.465±0.012	11.811±0.305
e		0.050 (TYP)	1.270(TYP)
L		0.0404±0.008	1.0255±0.203
L1		0.067±0.008	1.702 ±0.203
S		0.047 (MAX)	1.194 (MAX)
y		0.003(MAX)	0.076(MAX)
		0° 10°	0° 10°



28 pin 8x13.4mm STSOP Package Outline Dimension



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A	0.047 (MAX)	1.20 (MAX)
A1	0.004 ±0.002	0.10 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
D	0.465 ±0.004	11.800 ±0.100
E	0.315 ±0.004	8.000 ±0.100
e	0.022 (TYP)	0.55 (TYP)
HD	0.528 ±0.008	13.40 ±0.20.
L1	0.0315 ±0.004	0.80 ±0.10
y	0.003 (MAX)	0.076 (MAX)
	0° 5°	0° 5°



ORDERING INFORMATION

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μA) typ.	PACKAGE
UT62256CPC-70	70	0.3mA	28PIN PDIP
UT62256CPC-70L	70	2μA	28PIN PDIP
UT62256CPC-70LL	70	1μA	28PIN PDIP
UT62256CSC-35	35	0.3mA	28PIN SOP
UT62256CSC-35L	35	2μA	28PIN SOP
UT62256CSC-35LL	35	1μA	28PIN SOP
UT62256CSC-70	70	0.3mA	28PIN SOP
UT62256CSC-70L	70	2μA	28PIN SOP
UT62256CSC-70LL	70	1μA	28PIN SOP
UT62256CLS-35	35	0.3mA	28PIN STSOP
UT62256CLS-35L	35	2μA	28PIN STSOP
UT62256CLS-35LL	35	1μA	28PIN STSOP
UT62256CLS-70	70	0.3mA	28PIN STSOP
UT62256CLS-70L	70	2μA	28PIN STSOP
UT62256CLS-70LL	70	1μA	28PIN STSOP

ORDERING INFORMATION (for lead free product)

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μA) typ.	PACKAGE
UT62256CPCL-70	70	0.3mA	28PIN PDIP
UT62256CPCL-70L	70	2μA	28PIN PDIP
UT62256CPCL-70LL	70	1μA	28PIN PDIP
UT62256CSCL-35	35	0.3mA	28PIN SOP
UT62256CSCL-35L	35	2μA	28PIN SOP
UT62256CSCL-35LL	35	1μA	28PIN SOP
UT62256CSCL-70	70	0.3mA	28PIN SOP
UT62256CSCL-70L	70	2μA	28PIN SOP
UT62256CSCL-70LL	70	1μA	28PIN SOP
UT62256CLSL-35	35	0.3mA	28PIN STSOP
UT62256CLSL-35L	35	2μA	28PIN STSOP
UT62256CLSL-35LL	35	1μA	28PIN STSOP
UT62256CLSL-70	70	0.3mA	28PIN STSOP
UT62256CLSL-70L	70	2μA	28PIN STSOP
UT62256CLSL-70LL	70	1μA	28PIN STSOP



Rev. 1.3

UTRON

UT62256C  
32K X 8 BIT LOW POWER CMOS SRAM

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